

Attorney's Docket No.: 14580-031001

Amendments to the Specification:

Please replace the paragraph beginning at page 6, line 20 with the following amended paragraph:

On the TEOS layer 1 ~~[[is]]~~ are elements 3 of a chemically inert and electrically insulating bottom isolation layer (e.g.  $\text{Al}_2\text{O}_3$  or  $\text{Ta}_2\text{O}_5$ ). Over the elements 3 are ferroelectric elements 5 of PZT and further elements 7 of the same chemically inert material which forms layer 3. The PZT elements 5 and elements 3, 7 were formed from respective layers of amorphous PZT and the non-conductive matter (e.g.  $\text{Al}_2\text{O}_3$ ) which were formed over the TEOS layer 1 (e.g. by sputtering, at least in the case of the PZT), and then etched (using masking elements, e.g. of TEOS which are not shown). Dry etching is the preferred etching technique here, to guarantee a well shaped structure with a high taper angle.

Please replace the paragraph beginning at page 6, line 20 with the following amended paragraph:

Note that  $\text{TiO}_2$  is usually an insulator if it is a ell-crystallized material with proper stoichiometry. Therefore the thickness of the layer  $\text{TiO}_2$  should be selected appropriately, taking into account that part of the Ti may be sucked into the PZT and incorporated into the lattice during the PZT crystallization process. Note that in Fig. ~~[[3]]~~ 1 there is a layer of  $\text{TiO}_2$  covering the upper surface of the TEOS 1 between the elements 3, and some of these areas may include the top surfaces of the plugs extending through the TEOS 1 (or, more usually, the top surfaces of diffusion barriers over the plugs), so if the  $\text{TiO}_2$  layer 9 is not removed before the conductive

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material (such as  $\text{IrO}_2$ ) is inserted between the elements 3 then the layer 9 should be thin enough not to electrically insulate the plug and the corresponding  $\text{IrO}_2$  element(s). Alternatively, before the gaps are filled with  $\text{IrO}_2$ , an etching sep can be performed during which  $\text{TiO}_2$  9 is removed from the TEOS layer 1 as well as from the top of the elements 7. A side effect of this might be that during the etching some of the  $\text{TiO}_2$  (if any remains) might be removed from the side walls of the PZT elements 5.